

FJNS7565

For Output Amplifier of Electronic Flash Unit

- Low Collector-Emitter Saturation Voltage
- High Performance at Low Supply Voltage



1.Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|------------------|---------------------------|-----------|-------|
| V _{CBO} | Collector-Base Voltage | 15 | V |
| V _{CEO} | Collector-Emitter Voltage | 10 | V |
| V _{EBO} | Emitter-Base Voltage | 7 | V |
| I _C | Collector Current | 5 | Α |
| P _C | Collector Dissipation | 0.55 | W |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -55 ~ 150 | °C |

Electrical Characteristics $T_C=25$ °C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|-------------------------------------|------|------|------|-------|
| BV _{CBO} | Collector-Base Voltage | $I_C = 10\mu A, I_E = 0$ | 15 | | | V |
| BV _{CEO} | Collector-Emitter Voltage | $I_C = 1 \text{mA}, I_B = 0$ | 10 | | | V |
| BV _{EBO} | Emitter Base Voltage | $I_C = 10\mu A, I_C = 0$ | 7 | | | V |
| I _{CBO} | Collector Cut-off Current | $V_{CB} = 15V, I_{E} = 0$ | | | 100 | nA |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = 5V, I_{C} = 0$ | | | 100 | nA |
| h _{FE1} | DC Current Gain | $V_{CE} = 2V, I_{C} = 0.5A$ | 450 | | 800 | |
| h_{FE2} | | $V_{CE} = 2V, I_{C} = 2A$ | 300 | | | |
| h_{FE3} | | $V_{CE} = 2V$, $I_C = 5A$ | 150 | | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_C = 3A, I_B = 60mA$ | | | 0.45 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_C = 3A, I_B = 60mA$ | | | 1.5 | V |
| C _{ob} | Collector Output Capacitance | $V_{CB} = 20V, I_{E} = 0, f = 1MHz$ | | 20 | | pF |

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Typical Characteristics

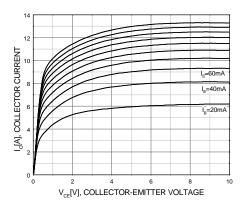


Figure 1. Static Characteristic

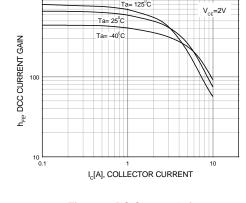


Figure 2. DC Current Gain

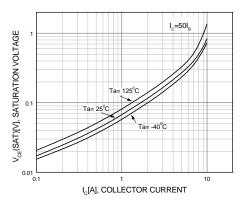


Figure 3. Collector-Emitter Saturation Voltage

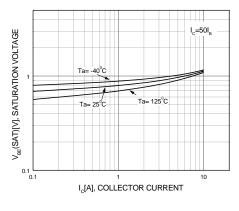


Figure 4. Base-Emitter Saturation Voltage

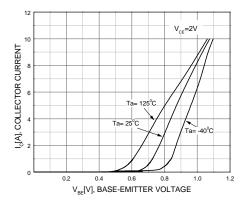


Figure 5. Base-Emitter On Voltage

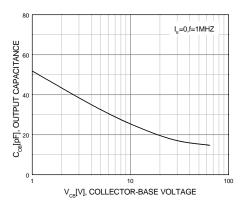
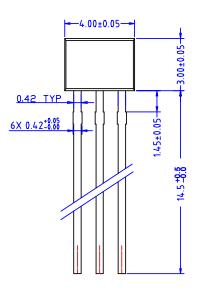


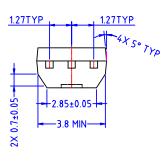
Figure 6. Collector Output Capacitance

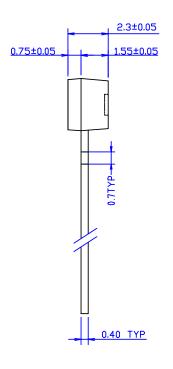
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Package Dimensions

TO-92Mini







Dimensions in Millimeters

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